NSN 5961-01-408-6786

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Inclosure Material: Plastic all transistor **Overall Length:** 0.210 inches all transistor **Overall Height:** 0.165 inches all transistor Overall Width: 0.205 inches all transistor **End Application:** 6625-01-363-6212 **Internal Configuration:** Field effect all transistor **Channel Polarity And Control Type (non-core):** N-channel junction type all transistor Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-92 all transistor **Component Function Relationship:** Matched **Component Name And Quantity:** 2 transistor **Mounting Method:** Terminal all transistor **Field Force Effect Type:** Electrostatic charge **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: -25.0 drain to gate voltage all transistor and -25.0 gate to source voltage all transistor **Current Rating Per Characteristic:** 10.00 milliamperes source cutoff current minor all transistor **Power Rating Per Characteristic:** 360.0 milliwatts small-signal input power, common-collector absolute all transistor **Maximum Operating Tempurature Per Measurement Point:** 135.0 degrees celsius ambient air all transistor **Test Data Document:** 34280-ps239115 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:**

N/a

Shelf Life:

Unit Of Measure:

3 uninsulated wire lead all transistor

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Demilitarization:

No

Fiig:

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